

L Number	Hits	Search Text	DB	Time stamp
1	4594	(memory dram\$1 sram\$1 rom\$1) and ((burie\$1 burying embed\$4) near3 (conduct\$3 metal\$3 polysilicon silicon si))	USPAT; EPO; JPO	2002/09/07 12:12
5	878	((memory dram\$1 sram\$1 rom\$1) and ((burie\$1 burying embed\$4) near3 (conduct\$3 metal\$3 polysilicon silicon si))) and epitaxial	USPAT; EPO; JPO	2002/09/07 12:13
9	219	((memory dram\$1 sram\$1 rom\$1) and ((burie\$1 burying embed\$4) near3 (conduct\$3 metal\$3 polysilicon silicon si))) and epitaxial) and (capacitor\$1 near3 ( groove\$1 opening\$1 aperture\$1 hole\$1 trench))	USPAT; EPO; JPO	2002/09/07 12:23